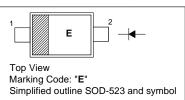
### SILICON EPITAXIAL PLANAR SCHOTTKY BARRIER DIODE

for rectifying small power application

#### **PINNING**

PIN	DESCRIPTION
1	Cathode
2	Anode



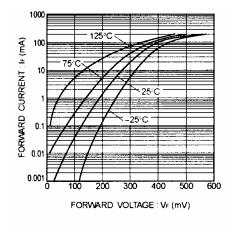
Absolute Maximum Ratings (T<sub>a</sub> = 25 °C)

Parameter	Symbol	Value	Unit
Reverse Voltage	$V_R$	30	V
Average Rectified Forward Current	Io	100	mA
Peak Forward Surge Current (60 Hz for 1 cyc.)	I <sub>FSM</sub>	1	А
Junction Temperature	T <sub>j</sub>	125	°C
Storage Temperature Range	T <sub>s</sub>	- 40 to + 125	°C

# Characteristics at T<sub>a</sub> = 25 °C

Parameter	Symbol	Max.	Unit
Forward Voltage at I <sub>F</sub> = 10 mA	V <sub>F</sub>	0.35	V
Reverse Current at V <sub>R</sub> = 10 V	I <sub>R</sub>	10	μΑ

Note: Please pay attention to static electricity when handling.



125°C REVERSE CURRENT: IR (A) 75°C 25°C -25°C REVERSE VOLTAGE: VR (V)

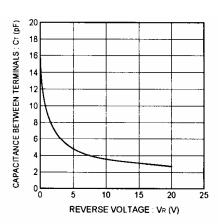


Fig.1 Forward characteristics

Fig.2 Reverse characteristics

Fig.3 Capacitance between terminals characteristics



# SEMTECH ELECTRONICS LTD.







### **PACKAGE OUTLINE**

## Plastic surface mounted package; 2 leads

**SOD-523** 

